



DMP6185SE-7 Information

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For Reference Only

Part Number DMP6185SE-7

Manufacturer Diodes Incorporated

Category

Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET PCH 60V 3A SOT223

Package TO-261-4, TO-261AA

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com

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Certified Quality

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DMP6185SE-7 Specifications

Manufacturer Part NumberDMP6185SE-7ManufacturerDiodes IncorporatedCategoryDiscrete Semiconductor ProductsTransistors - FETs, MOSFETs - SinglePackageTO-261-4, TO-261AASeriesAutomotive, AEC-Q101FET TypeP-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)60VCurrent - Continuous Drain (Id) @ 25°C3A (Ta)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id3V @ 250µAGate Charge (Qg) (Max) @ Vgs14nC @ 10VInput Capacitance (Ciss) (Max) @ Vds708pF @ 30VVgs (Max)±20VFET Feature-Power Dissipation (Max)1.2W (Ta)Rds On (Max) @ Id, Vgs150 mOhm @ 2.2A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageSOT-223Package / CaseTO-261-4, TO-261AAReport errors?		
Category Discrete Semiconductor Products Package TO-261-4, TO-261AA Series Automotive, AEC-Q101 FET Type P-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 60V Current - Continuous Drain (Id) @ 25°C 3A (Ta) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 3V @ 250µA Gate Charge (Qg) (Max) @ Vgs 14nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 708pF @ 30V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 1.2W (Ta) Rds On (Max) @ Id, Vgs 150 mOhm @ 2.2A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package SOT-223 Package / Case TO-261-4, TO-261AA	Manufacturer Part Number	DMP6185SE-7
Package TO-261-4, TO-261AA Series Automotive, AEC-Q101 FET Type P-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 60V Current - Continuous Drain (Id) @ 25°C 3A (Ta) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 3V @ 250μA Gate Charge (Qg) (Max) @ Vgs 14nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 708pF @ 30V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 1.2W (Ta) Rds On (Max) @ Id, Vgs 150 mOhm @ 2.2A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package SOT-223 Package / Case TO-261-4, TO-261AA	Manufacturer	Diodes Incorporated
Package TO-261-4, TO-261AA Series Automotive, AEC-Q101 FET Type P-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 60V Current - Continuous Drain (Id) @ 25°C 3A (Ta) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 3V @ 250μA Gate Charge (Qg) (Max) @ Vgs 14nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 708pF @ 30V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 1.2W (Ta) Rds On (Max) @ Id, Vgs 150 mOhm @ 2.2A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package SOT-223 Package / Case TO-261-4, TO-261AA	Category	Discrete Semiconductor Products
Series Automotive, AEC-Q101 FET Type P-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 3A (Ta) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 3V @ 250µA Gate Charge (Qg) (Max) @ Vgs 14nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 708pF @ 30V Vgs (Max) ±20V FET Feature Power Dissipation (Max) 1.2W (Ta) Rds On (Max) @ Id, Vgs 150 mOhm @ 2.2A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package SOT-223 Package / Case TO-261AA		Transistors - FETs, MOSFETs - Single
FET TypeP-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)60VCurrent - Continuous Drain (Id) @ 25°C3A (Ta)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id3V @ 250μAGate Charge (Qg) (Max) @ Vgs14nC @ 10VInput Capacitance (Ciss) (Max) @ Vds708pF @ 30VVgs (Max)±20VFET Feature-Power Dissipation (Max)1.2W (Ta)Rds On (Max) @ Id, Vgs150 mOhm @ 2.2A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageSOT-223Package / CaseTO-261-4, TO-261AA	Package	TO-261-4, TO-261AA
Technology Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 3A (Ta) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 150 mOhm @ 2.2A, 10V Operating Temperature Supplier Device Package Package / Case MOSFET (Metal Oxide) 60V 60V 60V 14n (Call) 15n (Cal	Series	Automotive, AEC-Q101
Drain to Source Voltage (Vdss)60VCurrent - Continuous Drain (Id) @ 25°C3A (Ta)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id3V @ 250μAGate Charge (Qg) (Max) @ Vgs14nC @ 10VInput Capacitance (Ciss) (Max) @ Vds708pF @ 30VVgs (Max)±20VFET Feature-Power Dissipation (Max)1.2W (Ta)Rds On (Max) @ Id, Vgs150 mOhm @ 2.2A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageSOT-223Package / CaseTO-261-4, TO-261AA	FET Type	P-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 150 mOhm @ 2.2A, 10V Operating Temperature Supplier Device Package Package / Case 3A (Ta) 3A (Ta) 3A (Ta) 3A (Ta) 3B (Ta) 3V @ 250µA 14nC @ 10V 708pF @ 30V F20V F20V F20V F20V F20V F30F (Fature) -55°C ~ 150°C (TJ) Surface Mount Supplier Device Package F30F (Case) T0-261-4, T0-261AA	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id 3V @ 250μA Gate Charge (Qg) (Max) @ Vgs 14nC @ 10V Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ±20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 150 mOhm @ 2.2A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case TO-261-4, TO-261AA	Drain to Source Voltage (Vdss)	60V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 150 mOhm @ 2.2A, 10V Operating Temperature Surplier Device Package Package / Case TO-261-4, TO-261AA	Current - Continuous Drain (Id) @ 25°C	3A (Ta)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 708pF @ 30V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 150 mOhm @ 2.2A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case TO-261-4, TO-261AA	Drive Voltage (Max Rds On, Min Rds On)	4.5V, 10V
Input Capacitance (Ciss) (Max) @ Vds 708pF @ 30V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 150 mOhm @ 2.2A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case TO-261-4, TO-261AA	Vgs(th) (Max) @ Id	3V @ 250μA
Vgs (Max)±20VFET Feature-Power Dissipation (Max)1.2W (Ta)Rds On (Max) @ Id, Vgs150 mOhm @ 2.2A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageSOT-223Package / CaseTO-261-4, TO-261AA	Gate Charge (Qg) (Max) @ Vgs	14nC @ 10V
FET Feature - Power Dissipation (Max) 1.2W (Ta) Rds On (Max) @ Id, Vgs 150 mOhm @ 2.2A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package SOT-223 Package / Case TO-261-4, TO-261AA	Input Capacitance (Ciss) (Max) @ Vds	708pF @ 30V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 150 mOhm @ 2.2A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case TO-261-4, TO-261AA	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs150 mOhm @ 2.2A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageSOT-223Package / CaseTO-261-4, TO-261AA	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package SOT-223 Package / Case TO-261-4, TO-261AA	Power Dissipation (Max)	1.2W (Ta)
Mounting Type Surface Mount Supplier Device Package SOT-223 Package / Case TO-261-4, TO-261AA	Rds On (Max) @ Id, Vgs	150 mOhm @ 2.2A, 10V
Supplier Device Package SOT-223 Package / Case TO-261-4, TO-261AA	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-261-4, TO-261AA	Mounting Type	Surface Mount
	Supplier Device Package	SOT-223
Report errors?	Package / Case	TO-261-4, TO-261AA
		Report errors?

DMP6185SE-7 Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

DMP6185SE-7 Payment Methods





















DMP6185SE-7 Shipping Methods













If you have any question about DMP6185SE-7, please do not hesitate to contact us!

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